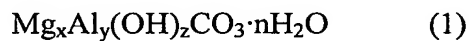


CLAIMS

1. An epoxy resin composition for encapsulating semiconductors comprising (A) an epoxy resin, (B) a phenol resin, (C) an inorganic filler, (D) a curing accelerator, (E) a
5 glycerol tri-fatty acid ester produced by dehydration condensation reaction of glycerol and a saturated fatty acid with a carbon atom content of 24-36, and (F) a hydrotalcite compound.

2. The epoxy resin composition for encapsulating semiconductors according to
10 claim 1, wherein the hydrotalcite compound is a compound shown by the following formula (1) and/or its sintered material,



wherein x, y, z, and n are positive numbers.

15 3. The epoxy resin composition for encapsulating semiconductors according to claim 2, wherein the hydrotalcite compound is a hydrotalcite of the above formula (1) in which $0.15 \leq (y/x+y) \leq 0.35$, $1.8 \leq (z/x+y) \leq 2.5$, and $0 \leq n \leq 5$ and/or its sintered material.

4. The epoxy resin composition for encapsulating semiconductors according to
20 claim 1, wherein the hydrotalcite compound is a compound shown by the formula $\text{Mg}_6\text{Al}_2(\text{OH})_{16}\text{CO}_3 \cdot 4\text{H}_2\text{O}$.

5. A semiconductor device comprising a semiconductor element encapsulated using the epoxy resin composition according to any one of claims 1-4.

25